

## 300V HYPERFAST RECTIFIER

### MAJOR PRODUCT CHARACTERISTICS

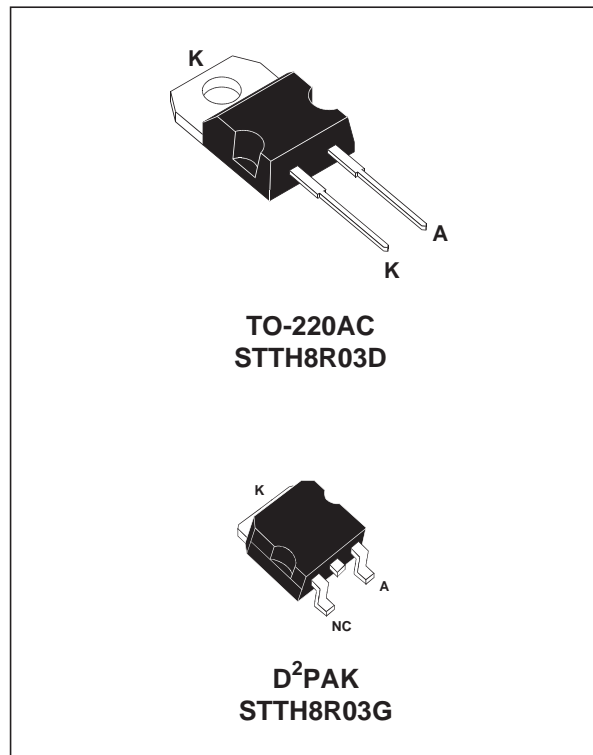
$I_{F(AV)}$	8 A
$V_{RRM}$	300 V
$I_{RM}$ (typ.)	4A
$T_j$ (max)	175 °C
$V_F$ (max)	1.3 V
$t_{rr}$ (max)	30 ns

### FEATURES AND BENEFITS

- Designed for high frequency applications.
- Hyperfast recovery competes with GaAs devices.
- Allows size decrease of snubbers and heatsinks.

### DESCRIPTION

The TURBOSWITCH "R" is an ultra high performance diode. This TURBOSWITCH family, which drastically cuts losses in associated MOSFET when run at high  $dI_F/dt$ , is suited for HF OFF-Line SMPS and DC/DC converters.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage		300	V
$I_{F(RMS)}$	RMS forward current		20	A
$I_{F(AV)}$	Average forward current	$T_c = 140^\circ\text{C} \quad \delta = 0.5$	8	A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10 \text{ ms sinusoidal}$	80	A
$T_{stg}$	Storage temperature range		- 65 + 175	°C
$T_j$	Maximum operating junction temperature		+ 175	°C

## STTH8R03G/D

### THERMAL AND POWER DATA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	2.5	°C/W

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions	Min.	Typ.	Max.	Unit	
$I_R^*$	Reverse leakage current	$V_R = V_{RRM}$	$T_j = 25^\circ\text{C}$			10	$\mu\text{A}$
			$T_j = 125^\circ\text{C}$		15	100	
$V_F^{**}$	Forward voltage drop	$I_F = 8\text{ A}$	$T_j = 25^\circ\text{C}$			1.8	V
			$T_j = 125^\circ\text{C}$		1.05	1.3	

Pulse test : \*  $t_p = 5\text{ ms}$ ,  $\delta < 2\%$

\*\*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 0.9 \times I_{F(AV)} + 0.05 I_{F(RMS)}^2$$

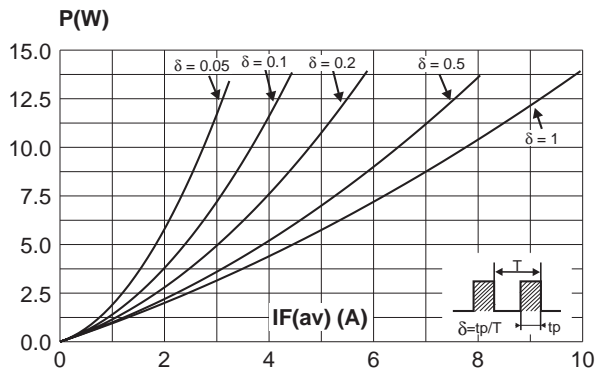
### RECOVERY CHARACTERISTICS

Symbol	Tests conditions	Min.	Typ.	Max.	Unit
$t_{rr}$	$I_F = 0.5\text{ A}$ $I_{rr} = 0.25\text{ A}$ $I_R = 1\text{ A}$		13	30	ns
	$I_F = 1\text{ A}$ $dI_F/dt = -50\text{ A}/\mu\text{s}$ $V_R = 30\text{ V}$				
$I_{RM}$	$V_R = 200\text{ V}$ $I_F = 8\text{ A}$ $dI_F/dt = -200\text{ A}/\mu\text{s}$		4	5.5	A
S factor			0.4		

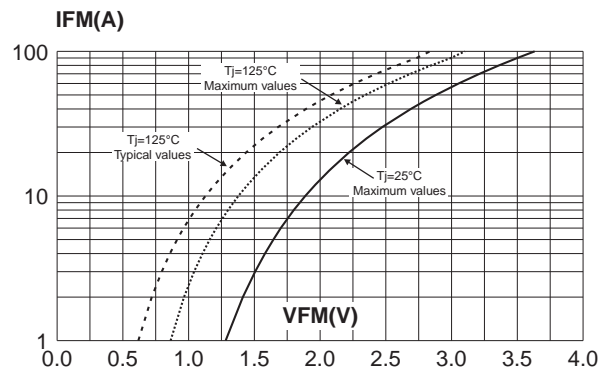
### TURN-ON SWITCHING CHARACTERISTICS

Symbol	Tests conditions	Min.	Typ.	Max.	Unit
$t_{fr}$	$T_j = 25^\circ\text{C}$ $I_F = 8\text{ A}$ $dI_F/dt = 100\text{ A}/\mu\text{s}$ measured at $1.1 \times V_{Fmax}$			200	ns
$V_{FP}$	$T_j = 25^\circ\text{C}$ $I_F = 8\text{ A}$ $dI_F/dt = 100\text{ A}/\mu\text{s}$			3.5	V

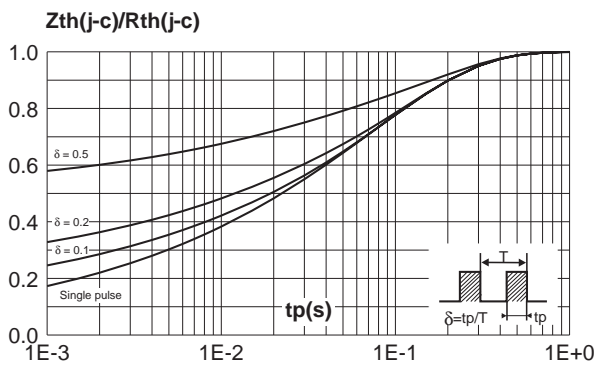
**Fig. 1:** Conduction losses versus average current



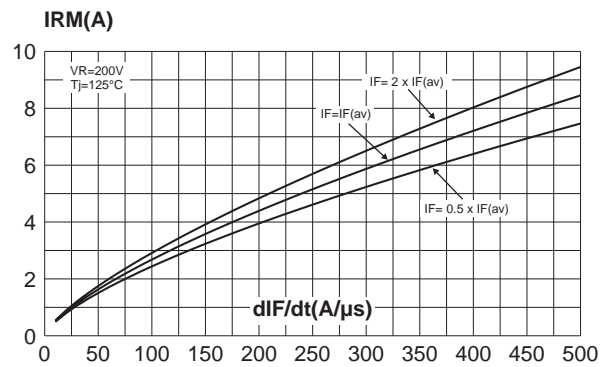
**Fig. 2:** Forward voltage drop versus forward current.



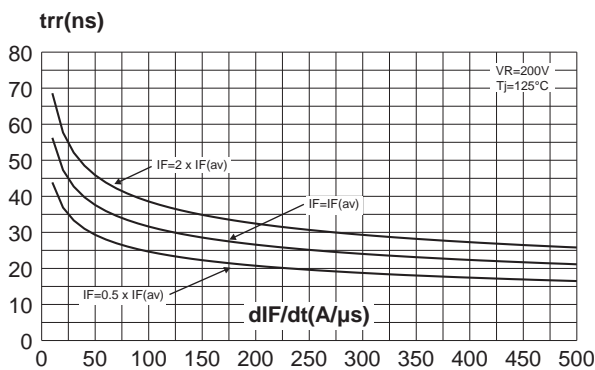
**Fig. 3:** Relative variation of thermal impedance junction to case versus pulse duration.



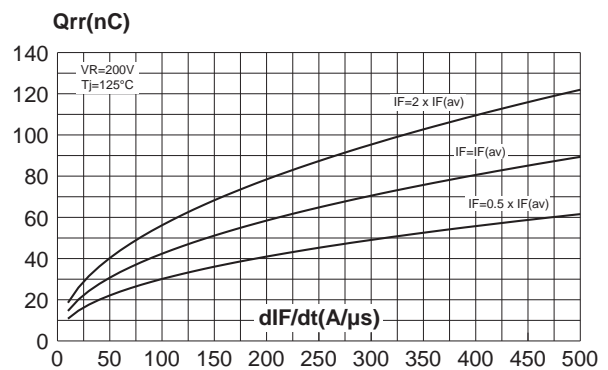
**Fig. 4:** Peak reverse recovery current versus dIF/dt (90% confidence).



**Fig. 5:** Reverse recovery time versus dIF/dt (90% confidence).

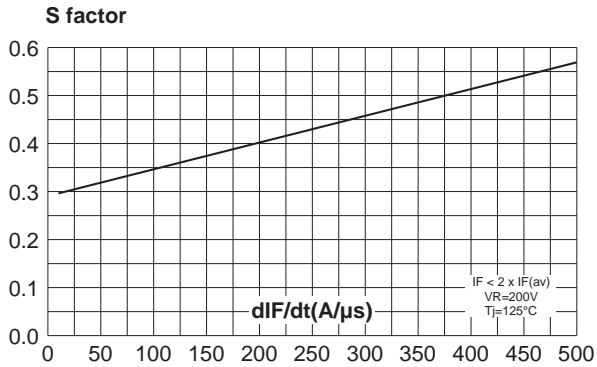


**Fig. 6:** Reverse recovery charges versus dIF/dt (90% confidence).

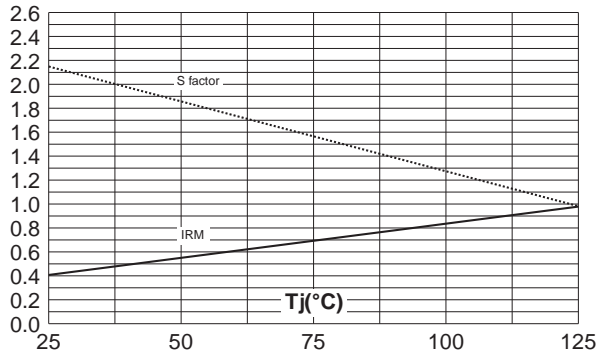


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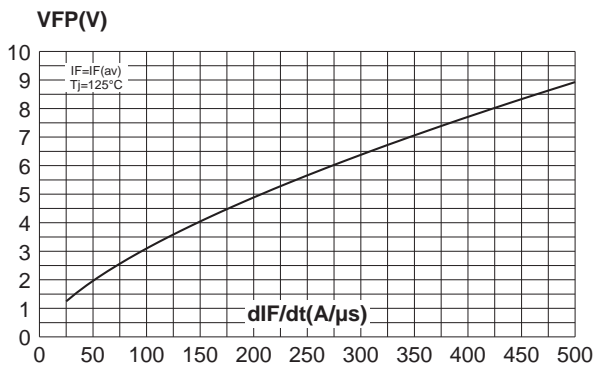
**Fig. 7:** Softness factor (tb/ta) versus dIF/dt (typical values).



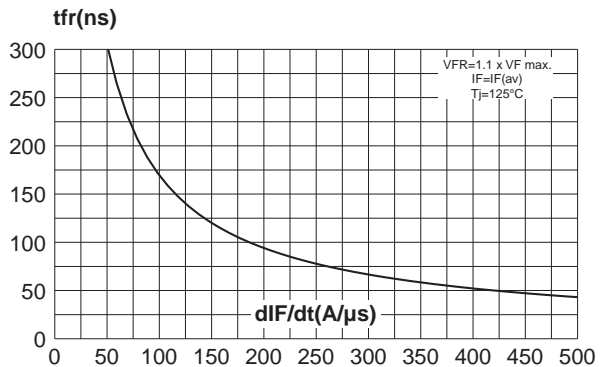
**Fig. 8:** Relative variation of dynamic parameters versus junction temperature (Reference: Tj=125°C).



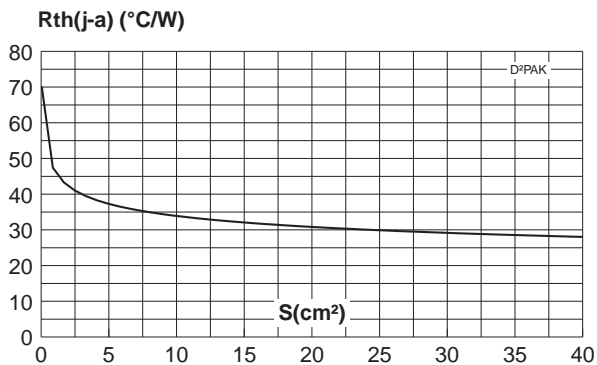
**Fig. 9:** Transient peak forward voltage versus dIF/dt (90% confidence).



**Fig. 10:** Forward recovery time versus dIF/dt (90% confidence).

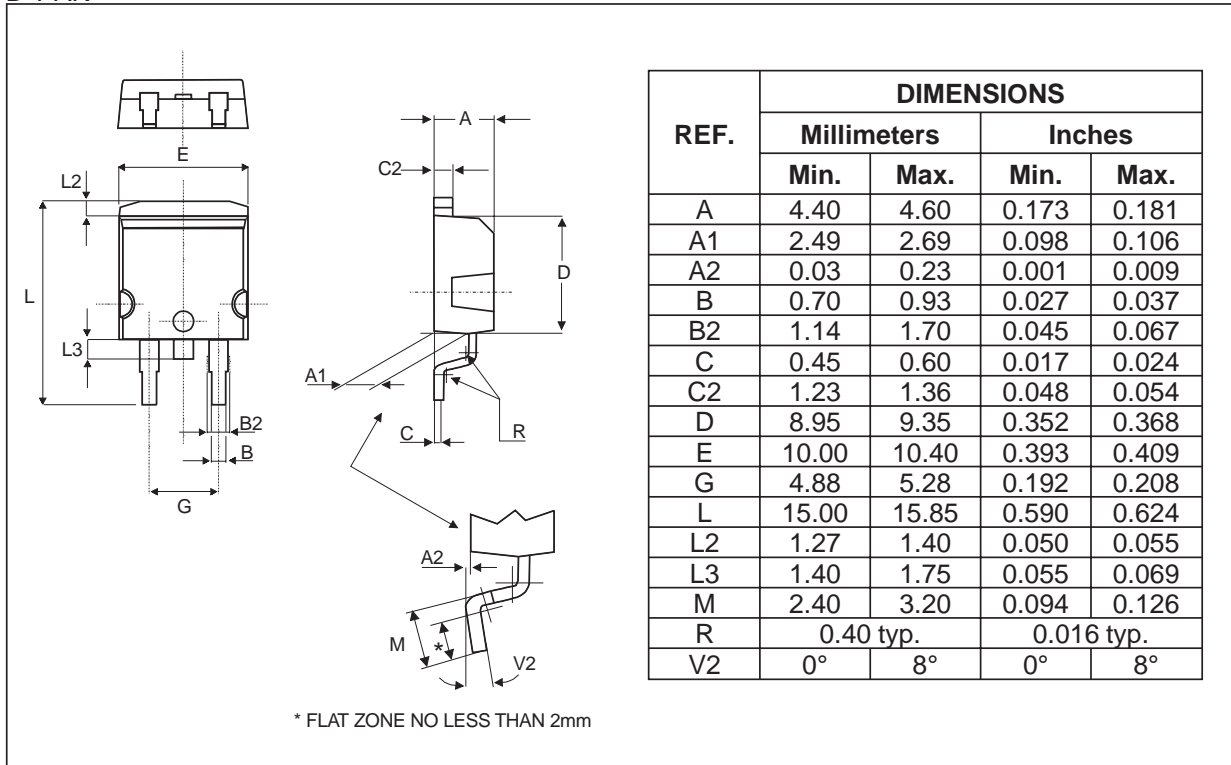


**Fig. 11:** Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35μm)(D<sup>2</sup>PAK)

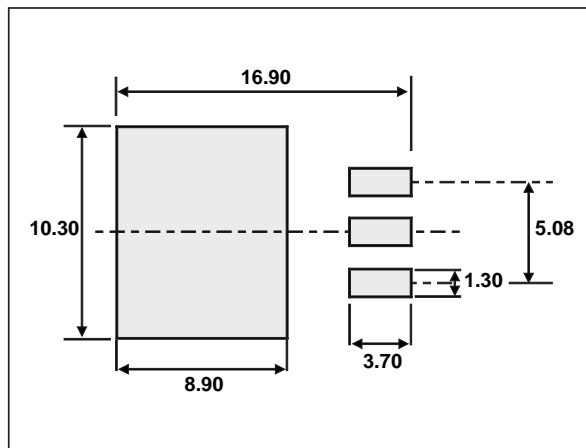


PACKAGE MECHANICAL DATA

D<sup>2</sup>PAK



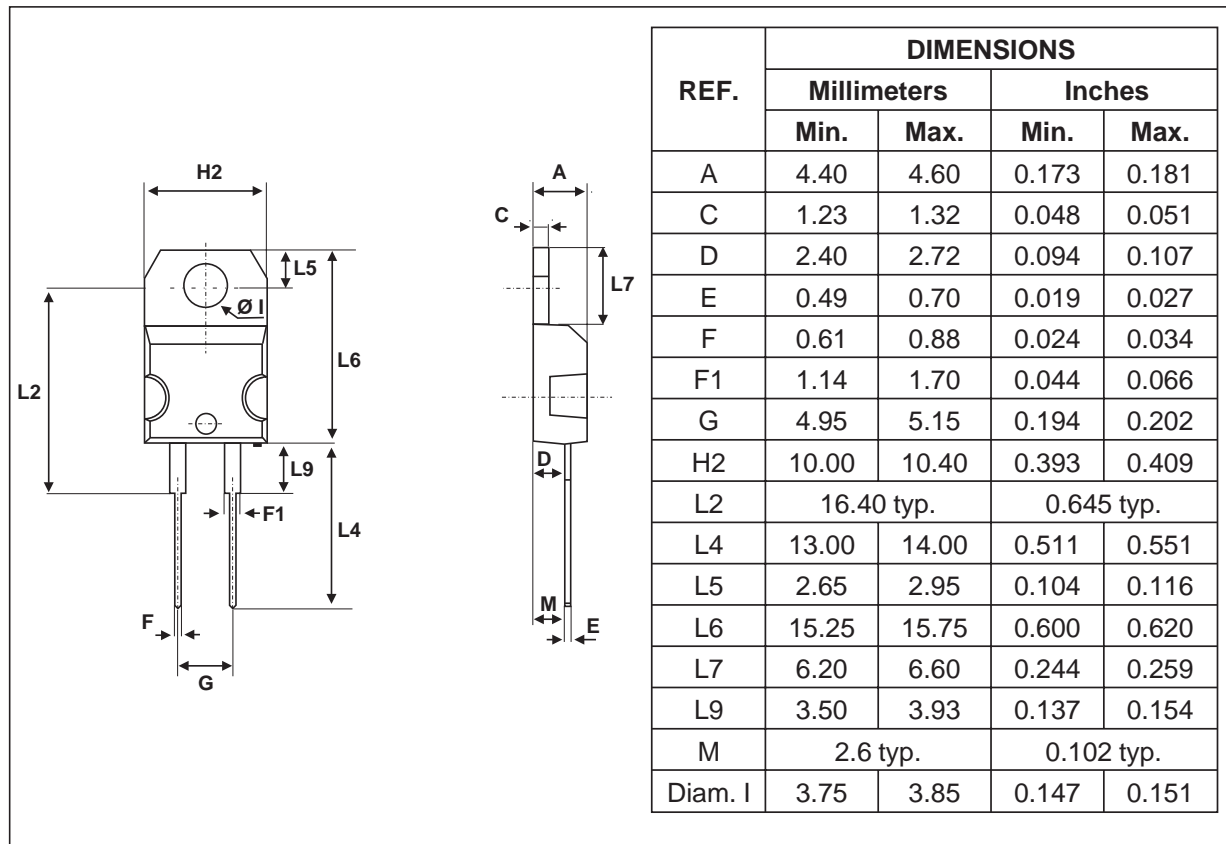
FOOTPRINT



# STTH8R03G/D

## PACKAGE MECHANICAL DATA

TO-220AC



Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH8R03D	STTH8R03D	TO-220AC	1.86g	50	Tube
STTH8R03G	STTH8R03G	D <sup>2</sup> PAK	1.48g	50	Tube
STTH8R03G-TR	STTH8R03G	D <sup>2</sup> PAK	1.48g	1000	Tape & Reel

- Cooling method: by conduction (C)
- Recommended torque value (TO-220AC): 0.55 N.m.
- Maximum torque value (TO-220AC): 0.7 N.m.
- Epoxy meets UL 94,V0

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